

/ Descriptions

TO-252 N MOS N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

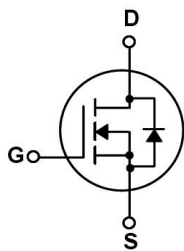
DS dv/dt
Low $R_{DS(ON)}$, Low gate charge, Low C_{rss} , Fast switching, Improved dv/dt capability.

/ Applications

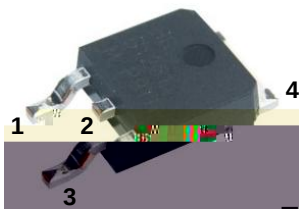
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S PIN 4 D

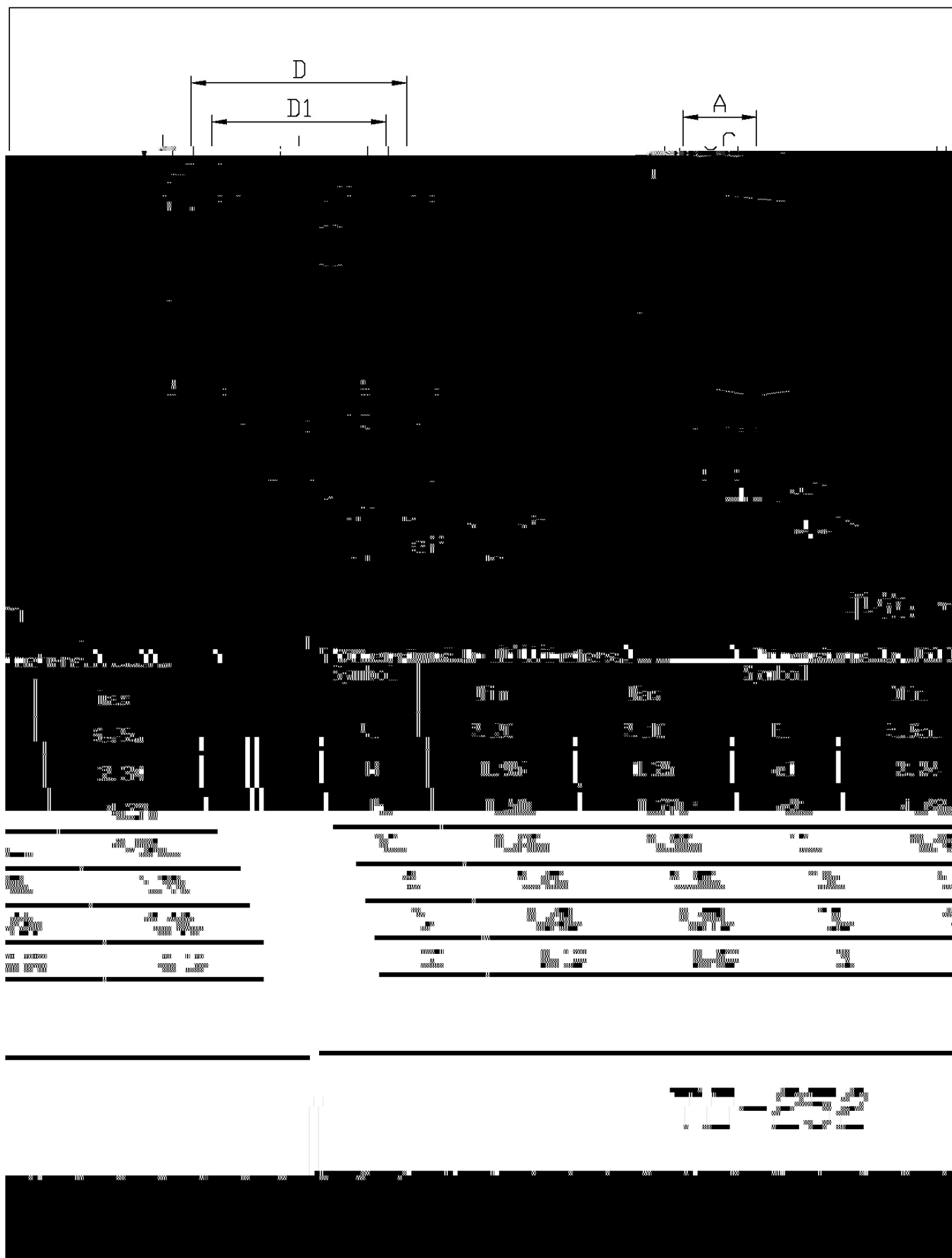
/ h_{FE} Classifications & Marking

See Marking Instructions.

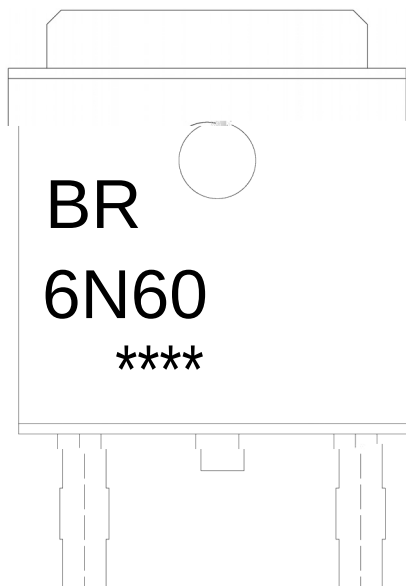
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	600	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	5.5	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	3.3	A
Drain Current - Pulsed	I_{DM}	22	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	300	mJ
Repetitive Avalanche Energy	E_{AR}	12.5	mJ
Avalanche Current	I_{AR}	5.5	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	40	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$ $V_{GS}=0V$ $V_{DS}=480V$ T_C			1	μA

/ Package Dimensions



/ Marking Instructions



BR

6N60

Note:

BR: Company Code

6N60: Product Type.

****: Lot No. Code, code change with Lot No.

